



16Mbyte(4Mx32) 72-pin SIMM EDO Mode, 4K Refresh, 5V
Part No. HMD4M32M2E, HMD4M32M2EG

GENERAL DESCRIPTION

The HMD4M32M2E is a 4M x 32 bit dynamic RAM high-density memory module. The module consists of two CMOS 4M x 16 bit DRAMs in 50-pin TSOP packages mounted on a 72-pin. A 0.1 or 0.22uF decoupling capacitor is mounted on the printed circuit board for each DRAM components. The module is a single In-line memory module with edge connections and is intended for mounting in to 72-pin edge connector sockets. All module components may be powered from a single 5V DC power supply. All inputs and outputs are TTL-compatible.

FEATURES

w Part Identification

HMD4M32M2E----4K Cycles/64ms Ref. Solder

HMD4M32M2EG- 4K Cycles/64ms Ref. Gold

w Access times : 50, 60ns

w High-density 16MByte design

w Single +5V± 0.5V power supply

w JEDEC standard pinout

w EDO Mode operation

w TTL compatible inputs and outputs

w FR4-PCB design

OPTIONS

w Timing

50ns access -5

60ns access -6

w Packages

72-pin SIMM M

MARKING

PRESENCE DETECT PINS

| Pin | 50ns | 60ns |
|-----|------|------|
| PD1 | Vss | Vss |
| PD2 | NC | NC |
| PD3 | Vss | NC |
| PD4 | Vss | NC |

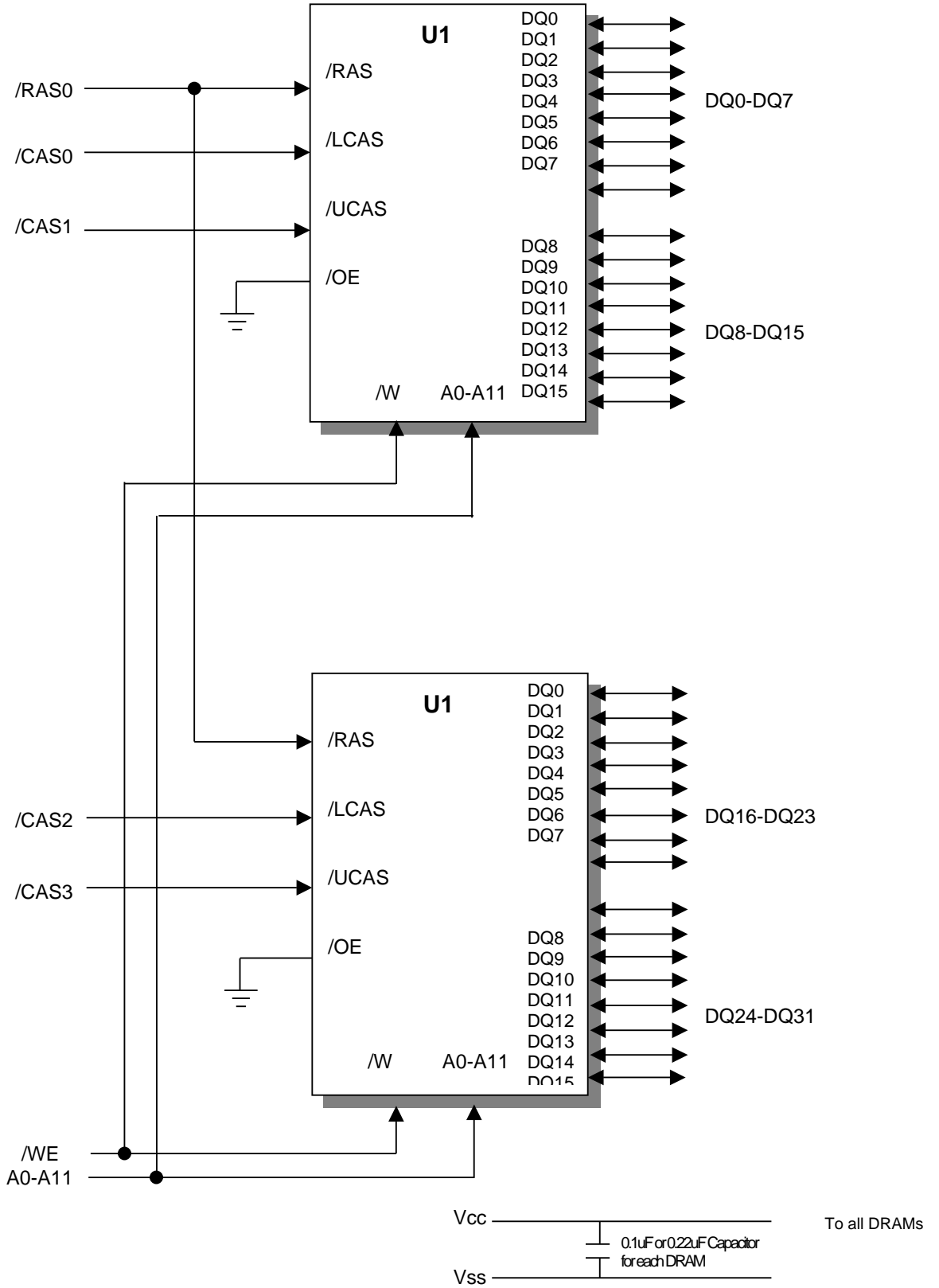
PERFORMANCE RANGE

| Speed | tRAC | tCAC | tRC | tHPC |
|-------|------|------|-------|------|
| 5 | 50ns | 13ns | 90ns | 26ns |
| 6 | 60ns | 15ns | 110ns | 30ns |

PIN ASSIGNMENT

| PIN | SYMBOL | PIN | SYMBOL | PIN | SYMBOL |
|-----|--------|-----|--------|-----|--------|
| 1 | Vss | 25 | DQ22 | 49 | DQ8 |
| 2 | DQ0 | 26 | DQ7 | 50 | DQ24 |
| 3 | DQ16 | 27 | DQ23 | 51 | DQ9 |
| 4 | DQ1 | 28 | A7 | 52 | DQ25 |
| 5 | DQ17 | 29 | A11 | 53 | DQ10 |
| 6 | DQ2 | 30 | Vcc | 54 | DQ26 |
| 7 | DQ18 | 31 | A8 | 55 | DQ11 |
| 8 | DQ3 | 32 | A9 | 56 | DQ27 |
| 9 | DQ19 | 33 | NC | 57 | DQ12 |
| 10 | Vcc | 34 | NC | 58 | DQ28 |
| 11 | NC | 35 | NC | 59 | Vcc |
| 12 | A0 | 36 | NC | 60 | DQ29 |
| 13 | A1 | 37 | NC | 61 | DQ13 |
| 14 | A2 | 38 | NC | 62 | DQ30 |
| 15 | A3 | 39 | Vss | 63 | DQ14 |
| 16 | A4 | 40 | /CAS0 | 64 | DQ31 |
| 17 | A5 | 41 | /CAS2 | 65 | DQ15 |
| 18 | A6 | 42 | /CAS3 | 66 | NC |
| 19 | A10 | 43 | /CAS1 | 67 | PD1 |
| 20 | DQ4 | 44 | /RAS0 | 68 | PD2 |
| 21 | DQ20 | 45 | NC | 69 | PD3 |
| 22 | DQ5 | 46 | NC | 70 | PD4 |
| 23 | DQ21 | 47 | /WE | 71 | NC |
| 24 | DQ6 | 48 | NC | 72 | Vss |

FUNCTIONAL BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | RATING |
|---------------------------------------|---------------|----------------|
| Voltage on Any Pin Relative to Vss | V_{IN_OUT} | -1V to 7.0V |
| Voltage on Vcc Supply Relative to Vss | Vcc | -1V to 7.0V |
| Power Dissipation | P_D | 2W |
| Storage Temperature | T_{STG} | -55°C to 150°C |
| Short Circuit Output Current | I_{OS} | 50mA |

w Permanent device damage may occur if " Absolute Maximum Ratings" are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED DC OPERATING CONDITIONS

(Voltage reference to V_{SS}, T_A=0 to 70 ° C)

| PARAMETER | SYMBOL | MIN | TYP. | MAX | UNIT |
|--------------------|----------|------|------|-------|------|
| Supply Voltage | Vcc | 4.5 | 5.0 | 5.5 | V |
| Ground | Vss | 0 | 0 | 0 | V |
| Input High Voltage | V_{IH} | 2.4 | - | Vcc+1 | V |
| Input Low Voltage | V_{IL} | -1.0 | - | 0.8 | V |

DC AND OPERATING CHARACTERISTICS

| SYMBOL | SPEED | MIN | MAX | UNITS |
|------------|-------|-----|-----|-------|
| I_{CC1} | -5 | - | 880 | mA |
| | -6 | - | 800 | mA |
| I_{CC2} | | - | 16 | mA |
| I_{CC3} | -5 | - | 880 | mA |
| | -6 | - | 800 | mA |
| I_{CC4} | -5 | - | 880 | mA |
| | -6 | - | 800 | mA |
| I_{CC5} | | - | 8 | mA |
| I_{CC6} | -5 | - | 880 | mA |
| | -6 | - | 800 | mA |
| $I_{I(L)}$ | | -40 | 40 | μA |
| $I_{O(L)}$ | | -5 | 5 | μA |
| V_{OH} | | 2.4 | - | V |
| V_{OL} | | - | 0.4 | V |

I_{CC1} : Operating Current * (/RAS , /CAS , Address cycling @ $t_{RC}=\min.$)

I_{CC2} : Standby Current (/RAS=/CAS= V_{IH})

I_{CC3} : /RAS Only Refresh Current * (/CAS= V_{IH} , /RAS, Address cycling @ $t_{RC}=\min$)

I_{CC4} : EDO Mode Current * (/RAS= V_{IL} , /CAS, Address cycling @ $t_{PC}=\min$)

I_{CC5} : Standby Current (/RAS=/CAS= $V_{CC}-0.2V$)

I_{CC6} : /CAS-Before-/RAS Refresh Current * (/RAS and /CAS cycling @ $t_{RC}=\min$)

I_{IL} : Input Leakage Current (Any input $0V \leq V_{IN} \leq 6.5V$, all other pins not under test = 0V)

I_{OL} : Output Leakage Current (Data out is disabled, $0V \leq V_{OUT} \leq 5.5V$)

V_{OH} : Output High Voltage Level ($I_{OH} = -5mA$)

V_{OL} : Output Low Voltage Level ($I_{OL} = 4.2mA$)

* **NOTE:** I_{CC1} , I_{CC3} , I_{CC4} and I_{CC6} are dependent on output loading and cycle rates. Specified values are obtained with the output open. I_{CC} is specified as an average current. In I_{CC1} and I_{CC3} , address can be changed maximum once while /RAS= V_{IL} . In I_{CC4} , address can be changed maximum once within one page mode cycle.

CAPACITANCE ($T_A=25^\circ C$, $V_{CC} = 5V$, $f = 1Mz$)

| DESCRIPTION | SYMBOL | MIN | MAX | UNITS |
|-----------------------------------|-----------|-----|-----|-------|
| Input Capacitance (A0-A10) | C_{IN1} | - | 64 | pF |
| Input Capacitance (/W) | C_{IN2} | - | 70 | pF |
| Input Capacitance (/RAS0) | C_{IN3} | - | 42 | pF |
| Input Capacitance (/CAS0-/CAS3) | C_{IN4} | - | 30 | pF |
| Input/Output Capacitance (DQ0-31) | C_{DQ1} | - | 17 | pF |

AC CHARACTERISTICS ($0^\circ C \leq T_A \leq 70^\circ C$, $V_{CC} = 5V \pm 10\%$, See notes 1,2.)

| STANDARD OPERATION | SYMBOL | -5 | | -6 | | UNIT |
|--|-----------|-----|-----|-----|-----|------|
| | | MIN | MAX | MIN | MAX | |
| Random read or write cycle time | t_{RC} | 90 | | 110 | | ns |
| Access time from /RAS | t_{RAC} | | 50 | | 60 | ns |
| Access time from /CAS | t_{CAC} | | 13 | | 15 | ns |
| Access time from column address | t_{AA} | | 25 | | 30 | ns |
| /CAS to output in Low-Z | t_{CLZ} | 3 | | 3 | | ns |
| Output buffer turn-off delay from /CAS | t_{CEZ} | 3 | 13 | 3 | 15 | ns |
| Transition time (rise and fall) | t_T | 2 | 50 | 2 | 50 | ns |
| /RAS precharge time | t_{RP} | 30 | | 40 | | ns |
| /RAS pulse width | t_{RAS} | 50 | 10K | 60 | 10K | ns |
| /RAS hold time | t_{RSH} | 13 | | 15 | | ns |
| /CAS hold time | t_{CSH} | 38 | | 45 | | ns |
| /CAS pulse width | t_{CAS} | 8 | 10K | 10 | 10K | ns |
| /RAS to /CAS delay time | t_{RCD} | 20 | 37 | 20 | 45 | ns |
| /RAS to column address delay time | t_{RAD} | 15 | 25 | 15 | 30 | ns |
| /CAS to /RAS precharge time | t_{CRP} | 5 | | 5 | | ns |

| | | | | | | |
|---|------------|----|------|----|------|----|
| Row address set-up time | t_{ASR} | 0 | | 0 | | ns |
| Row address hold time | t_{RAH} | 10 | | 10 | | ns |
| Column address set-up time | t_{ASC} | 0 | | 0 | | ns |
| Column address hold time | t_{CAH} | 8 | | 10 | | ns |
| Column address hold referenced to /RAS | t_{AR} | 40 | | 45 | | ns |
| Column Address to /RAS lead time | t_{RAL} | 25 | | 30 | | ns |
| Read command set-up time | t_{RCS} | 0 | | 0 | | ns |
| Read command hold referenced to /CAS | t_{RCH} | 0 | | 0 | | ns |
| Read command hold referenced to /RAS | t_{RRH} | 0 | | 0 | | ns |
| Write command hold time | t_{WCH} | 10 | | 10 | | ns |
| Write command hold referenced to /RAS | t_{WCR} | 40 | | 45 | | ns |
| Write command pulse width | t_{WP} | 10 | | 10 | | ns |
| Write command to /RAS lead time | t_{RWL} | 13 | | 15 | | ns |
| Write command to /CAS lead time | t_{CWL} | 8 | | 10 | | ns |
| Data-in set-up time | t_{DS} | 0 | | 0 | | ns |
| Data-in hold time | t_{DH} | 8 | | 10 | | ns |
| Data-in hold referenced to /RAS | t_{DHR} | 40 | | 45 | | ns |
| Refresh period | t_{REF} | | 64 | | 64 | ns |
| Write command set-up time | t_{WCS} | 0 | | 0 | | ns |
| /CAS to /W delay time | t_{CWD} | 36 | | 40 | | ns |
| /RAS to /W delay time | t_{RWD} | 73 | | 85 | | ns |
| /CAS precharge(C-B-R counter test) | t_{CPT} | 20 | | 20 | | ns |
| Column address to /W delay time | t_{AWD} | 48 | | 55 | | ns |
| Access time from /CAS precharge | t_{CPA} | | 30 | | 35 | ns |
| /CAS precharge time (Hyper Page cycle) | t_{CP} | 8 | | 10 | | ns |
| /RAS pulse width (Hyper Page cycle) | t_{RASP} | 50 | 200K | 60 | 200K | ns |
| /W to /RAS precharge time (C-B-R refresh) | t_{WRP} | 10 | | 10 | | ns |
| /W to /RAS hold time (C-B-R refresh) | t_{WRH} | 10 | | 10 | | ns |

NOTES

1. An initial pause of 200 μ s is required after power-up followed by any 8 /RAS-only or /CAS-before-/RAS refresh cycles before proper device operation is achieved.
2. $V_{IH(min)}$ and $V_{IL(max)}$ are reference levels for measuring timing of input signals. Transition times are measured between $V_{IH(min)}$ and $V_{IL(max)}$ and are assumed to be 5ns for all inputs.
3. Measured with a load equivalent to 1TTL loads and 100pF
4. Operation within the $t_{RCD(max)}$ limit insures that $t_{RAC(max)}$ can be met. $t_{RCD(max)}$ is specified as a reference point only. If t_{RCD} is greater than the specified $t_{RCD(max)}$ limit, then access time is controlled exclusively by t_{CAC} .
5. Assumes that $t_{RCD} \geq t_{RCD(max)}$
6. t_{AR} , t_{WCR} , t_{DHR} are referenced to $t_{RAD(max)}$
7. This parameter defines the time at which the output achieves the open circuit condition and is not referenced to V_{OH}

or V_{OL} .

8. t_{WCS} , t_{RWD} , t_{CWD} and t_{AWD} are non restrictive operating parameter.

They are included in the data sheet as electrical characteristic only. If $t_{WCS} \geq t_{WCS(min)}$ the cycle is an early write cycle and the data out pin will remain high impedance for the duration of the cycle.

9. Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.

10. These parameters are referenced to the /CAS leading edge in early write cycles and to the /W leading edge in read-write cycles.

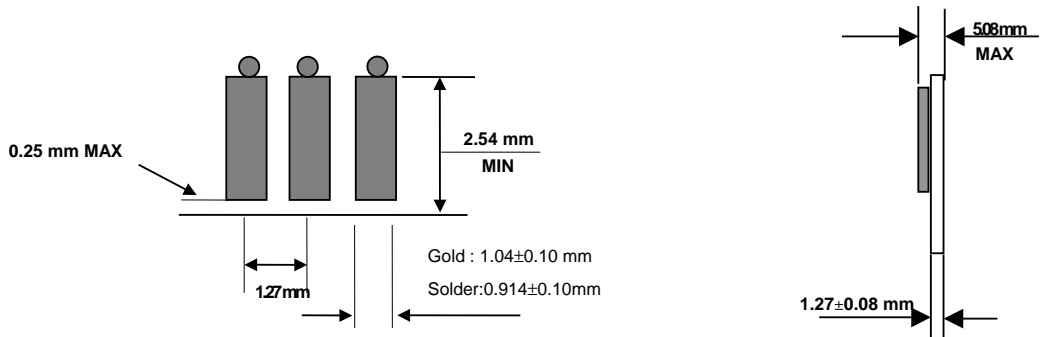
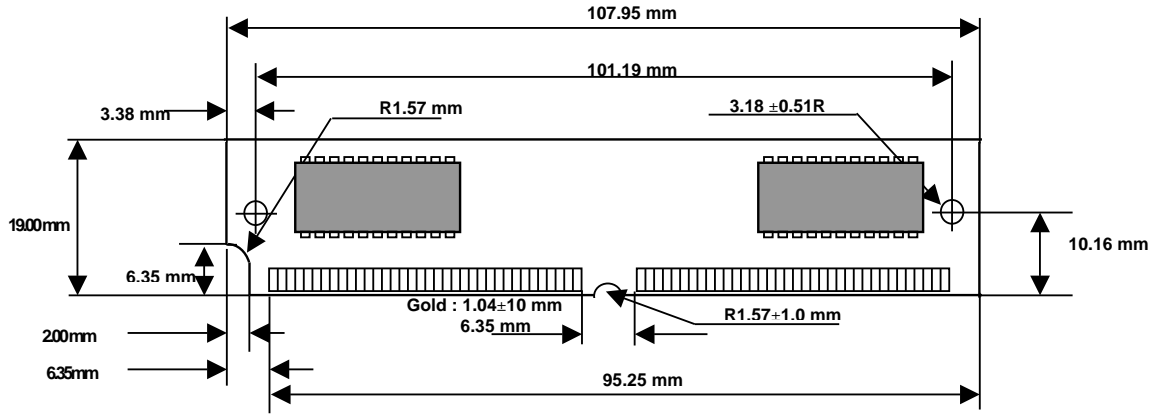
11. Operation within the $t_{RAD(max)}$ limit insures that $t_{RAC(max)}$ can be met. $t_{RAD(max)}$ is specified as a reference point only. If t_{RAD} is greater than the specified $t_{RAD(max)}$ limit, then access time is controlled by t_{AA} .

TIMING DIAGRAM

Please refer to attached timing diagram chart (I)

PACKAGING INFORMATION

SIMM Design



ORDERING INFORMATION

| Part Number | Density | Org. | Package | Refresh Cycle | Vcc | SPEED |
|---------------|---------|-----------|-------------|---------------------------|------|-------|
| HMD4M32M2EG-5 | 16MByte | 4MX 32bit | 72 Pin-SIMM | 4,096 Cycles 64ms Ref. | 5.0V | 50ns |
| HMD4M32M2EG-6 | 16MByte | 4MX 32bit | 72 Pin-SIMM | 4,096 Cycles 64ms Ref. | 5.0V | 60ns |